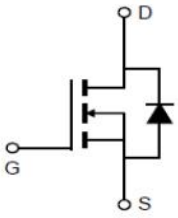
•General Description

The N-Channel MOSFET LH027N100 has the low $R_{DS(on)}$,low gate charge,fast switching and excellent avalanche characteristics.This device is suitable for Power Supplies and Li-Batterty.



V_{DS} =100V

$R_{DS(ON)}$ =2.7mΩ

I_D =180A

■ RoHS COMPLIANT

TO-220

TO-263

•Features

- ■High Efficiency
- ■Low $R_{DS(on)}$ & FOM
- ■100% EAS Guaranteed

•Application

- ■LED/LCD/PDP TV and monitor Lighting
- ■Power Supplies
- ■UPS
- ■DC-DC Converter

•Ordering Information:

Part Number	LH027N100	LH027N100
Package	TO-220	TO-263
Basic Ordering Unit (pcs)	1000	800
Normal Package Material Ordering Code	LH027N100T-TO220-TU	LH027N100T63-TO263-TAP
Halogen Free Ordering Code	LH027N100T-TO220-TU-HF	LH027N100T63-TO263-TAP-HF

•Absolute Maximum Ratings（TC =25℃）

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D(TC=25°C)	180	A
	I_D(TC=100°C)	120	A
Pulsed drain current (TC = 25°C, tp limited by Tjmax)[1]	I_D pulse	720	A
Single Pulse Avalanche Energy[2]	E_{AS}	1180	mJ
Power Dissipation(TC=25℃)	P_D	230	W
Operating Temperature	T_J	-55~+175	℃
Storage Temperature	T_{STG}	-55~+175	℃

●Electronic Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D=250uA	100	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250uA	2.0	--	4.0	V
Drain-source On Resistance[3]	$R_{DS(ON)}$	V_{GS} =10V, I_D=20A	--	2.7	3.2	mΩ
Drain-Source Leakage Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V,T_J=25℃	--	--	1	uA
		V_{DS}=80V,V_{GS}=0V,T_J=85℃	--	--	10	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20,V_{DS}=0V	--	--	±100	nA
Input Capacitance	Ciss	V_{GS} = 0V, V_{DS} = 50V f = 1.0MHz	--	5500	--	pF
Output Capacitance	Coss		--	3281	--	
Reverse transfer Capacitance	Crss		--	260	--	
Turn-on delay time	Td(on)	I_D =30A, V_{DS} = 80V V_{GS} = 10V V_G=4.5Ω	--	29	--	nS
Rise time	Tr		--	28	--	
Turn -Off Delay Time	Td(off)		--	88	--	
Fall time	Tf		--	32	--	
Total Gate Charge	Qg	I_D =50A, V_{DS} =30V V_{GS} = 10V	--	102	---	nC
Gate-to-Source Charge	Qgs		--	22	--	
Gate-to-Drain Charge	Qgd		--	33	---	
Continuous Diode Forward Current	I_S	--	--	--	180	A
Diode Forward Voltage	V_{SD}	Tj=25°C, Is=20.0A V_{GS} =0V	--	0.8	1.2	V
Reverse Recovery Time	trr	If=Is di_F/dt=100A/μs	--	79	--	ns
Reverse Recovery Charge	Qrr		--	137	--	nC

●Thermal Characteristics

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance Junction-case	Rth_{JC}	0.5	℃/W
Thermal Resistance Junction-ambient	Rth_{JA}	62	℃/W

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2.L= 1mH, I_{AS}=50A,V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C

3.Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

●Typical Characteristics

Fig1.Output Characteristics

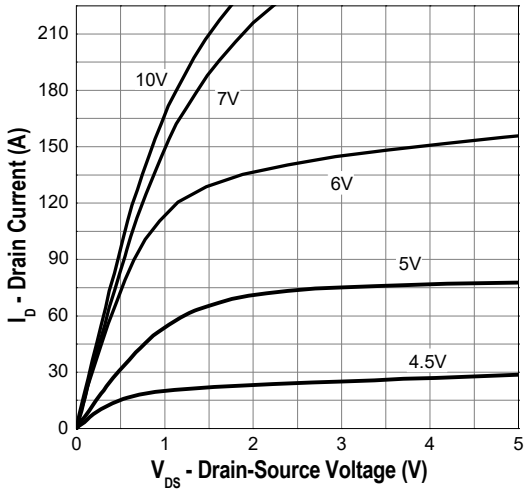


Fig2.Gate Threshold Voltage

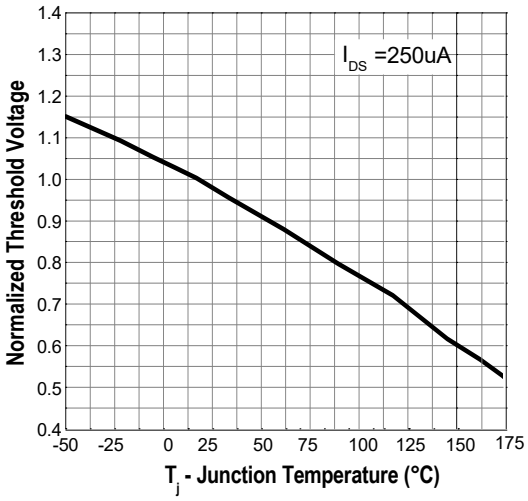


Fig3.Gate-Source On Resistance

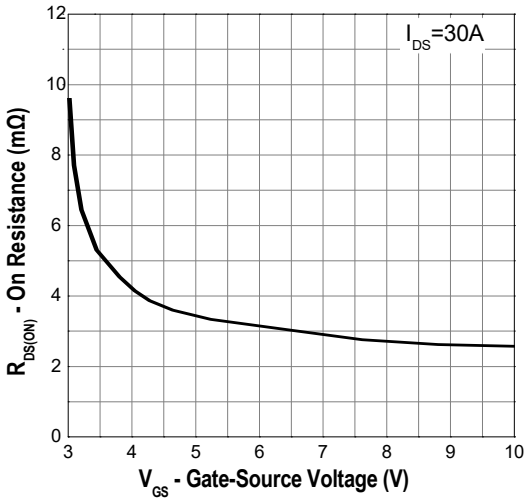


Fig4.Drain-Source On Resistance

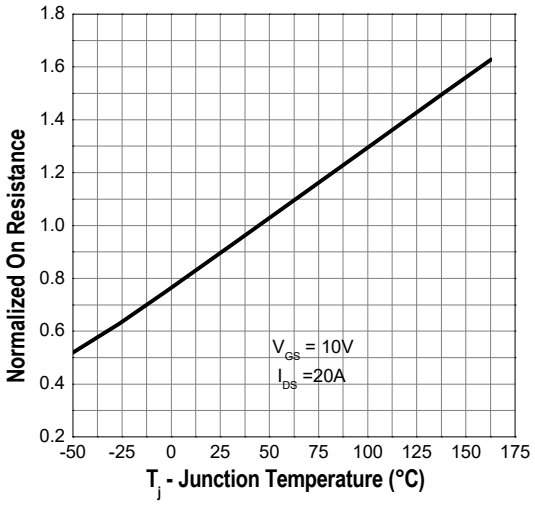


Fig5.Drain-Source On Resistance

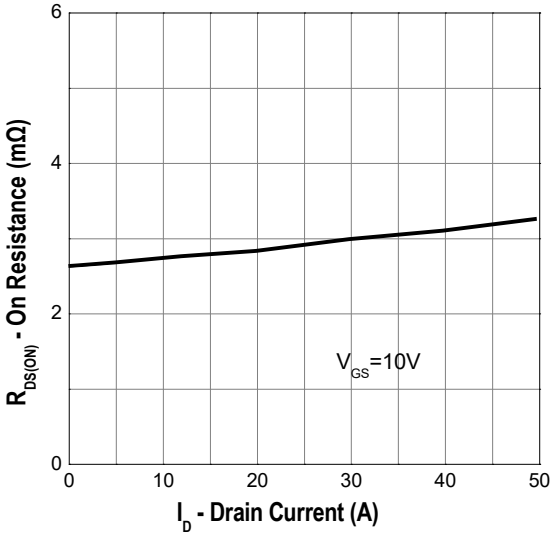
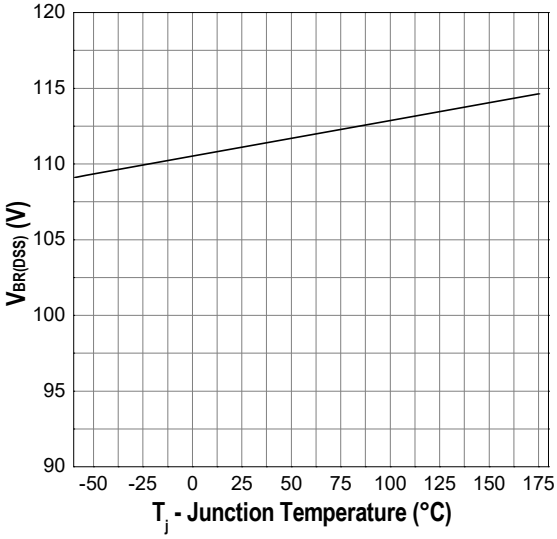


Fig6.Drain-source Breakdown Voltage



●Typical Characteristics(Cont .)

Fig7.Power Dissipation

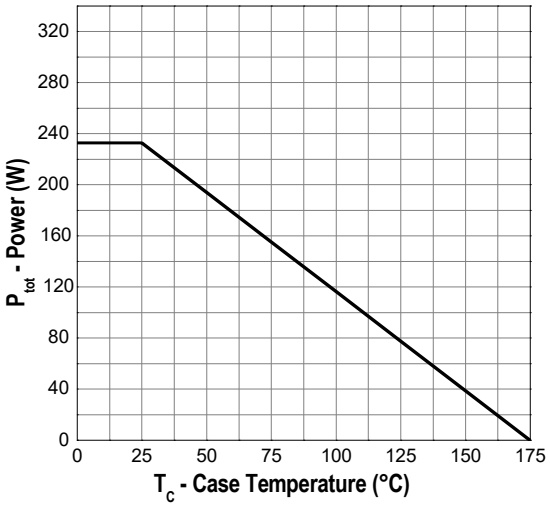


Fig8.Drain Current

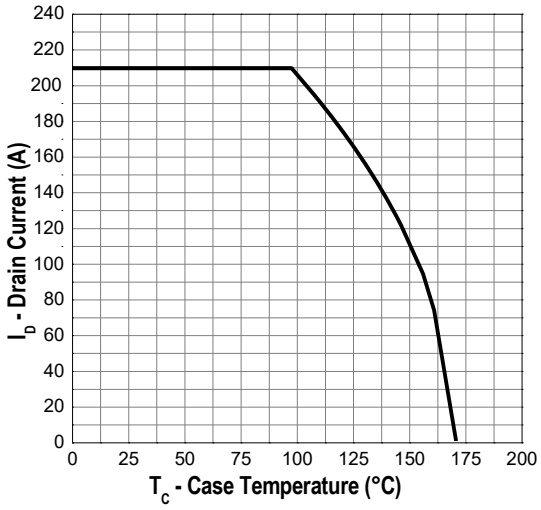


Fig9.Safe Operation Area

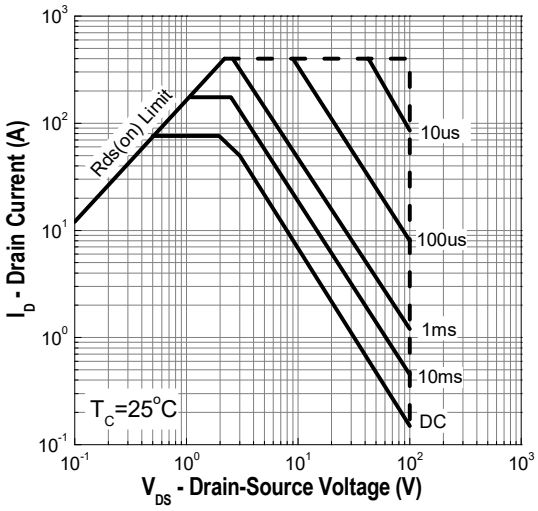


Fig10.Transient Thermal Impedance

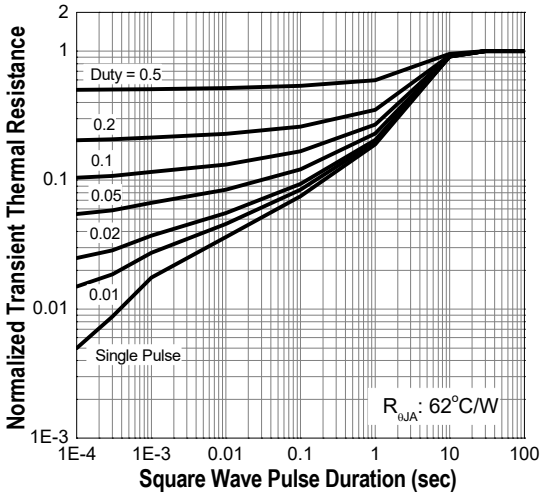


Fig11.Capacitance

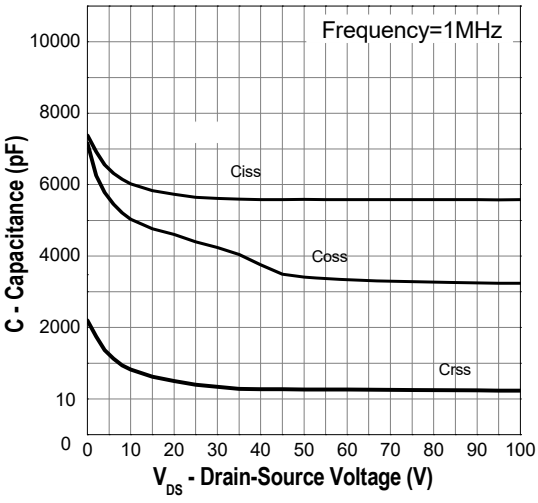
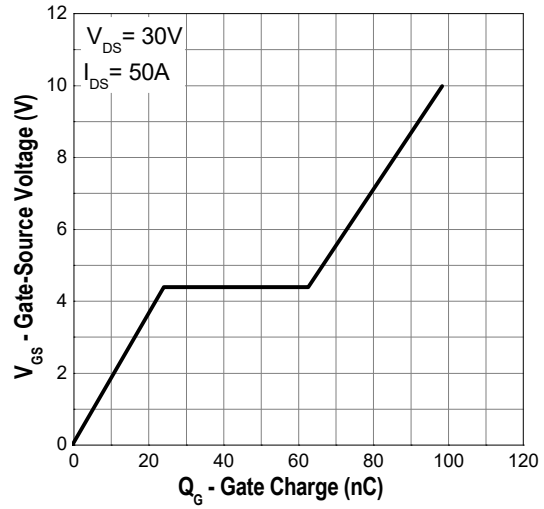


Fig12.Gate Charge



●Test Circuits & Waveforms

Fig1.Gate Charge Test Circuit & Waveform

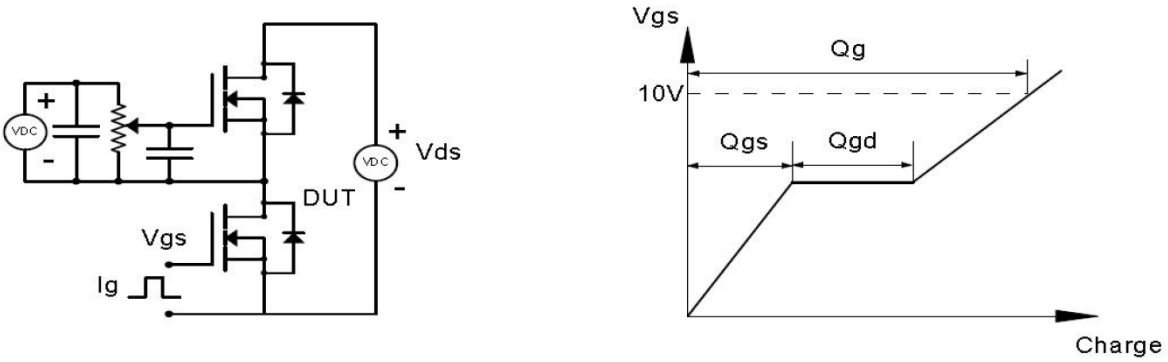


Fig2.Resistive Switching Test Circuit & Waveform

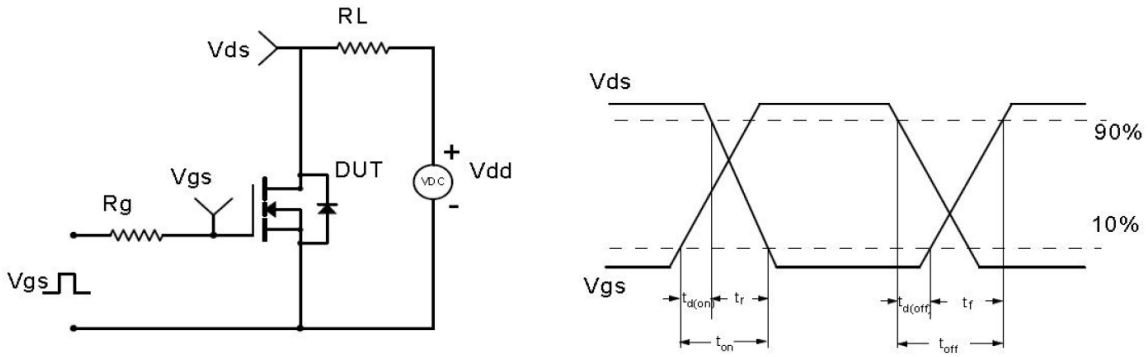


Fig3.Unclamped Inductive Switching Test Circuit & Waveform

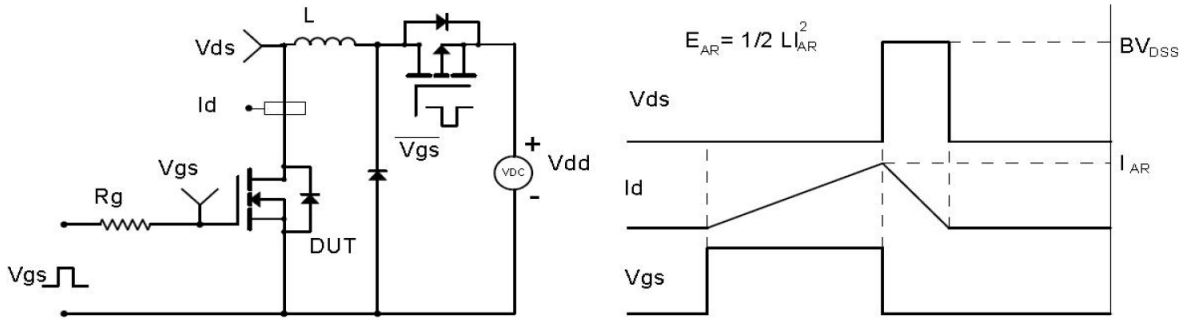
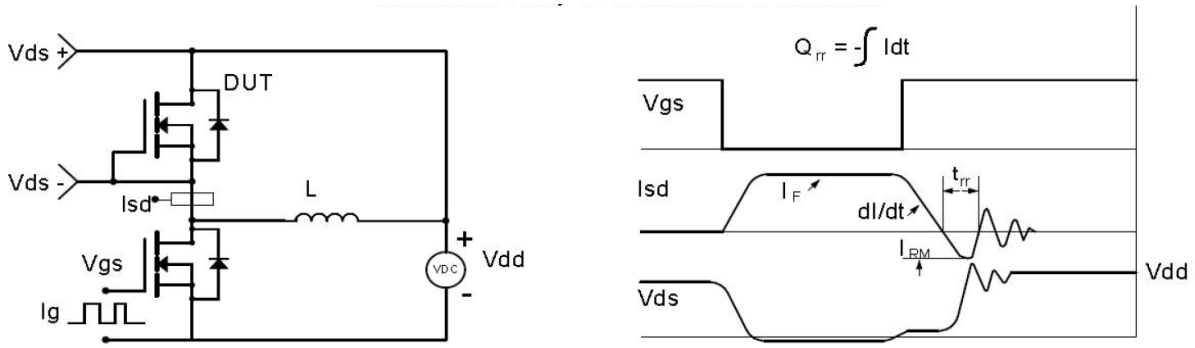


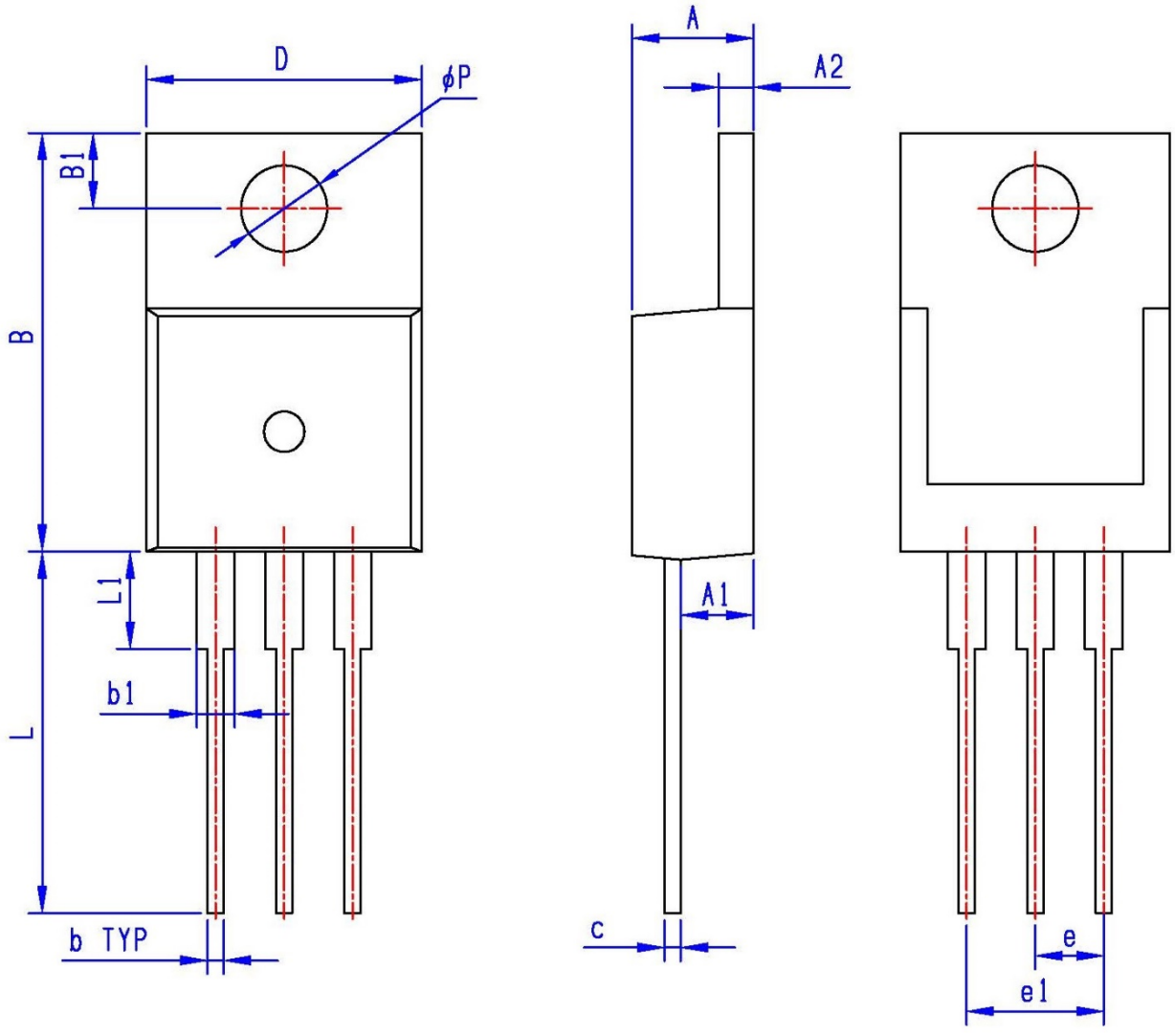
Fig4.Diode Recovery Switching Test Circuit & Waveform



●Dimensions（TO-220)

UNIT:mm

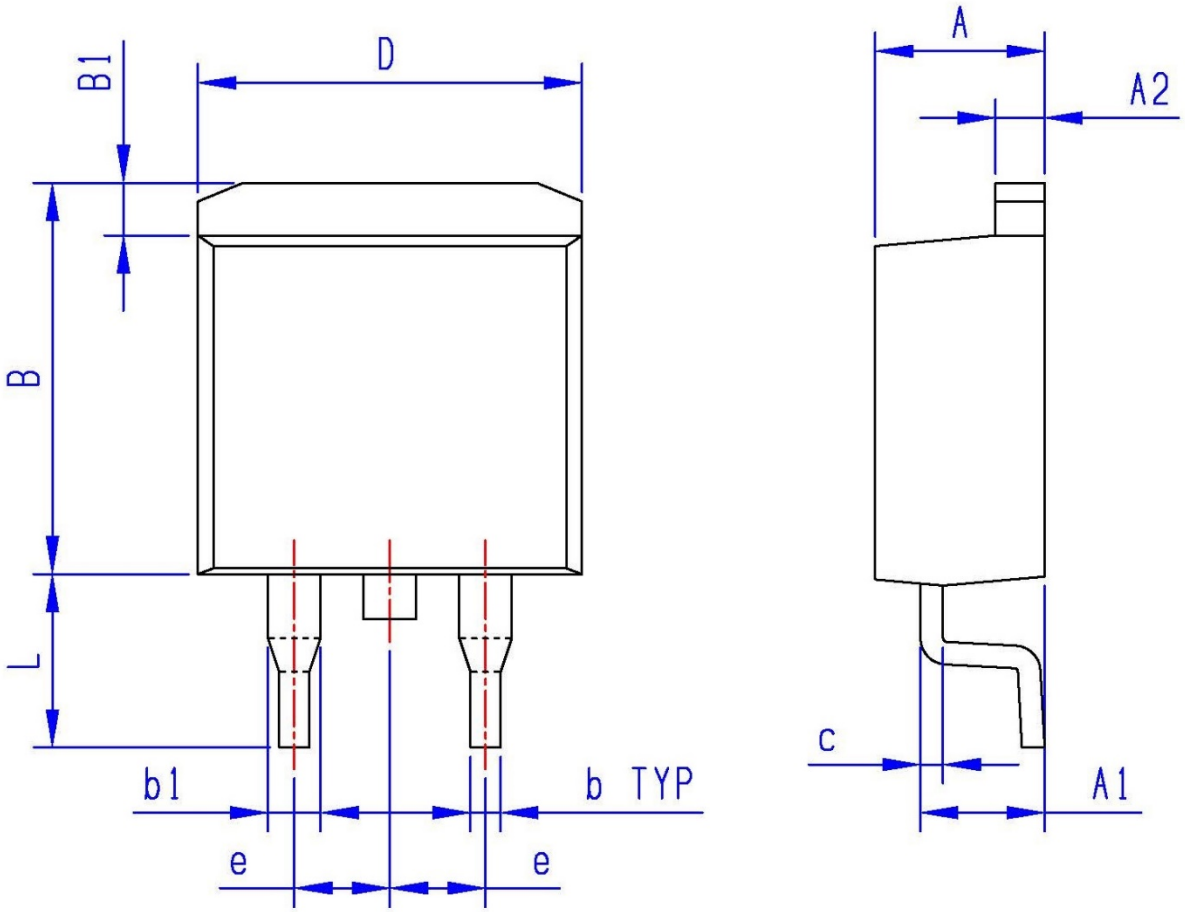
SYMBOL	min	max	SYMBOL	min	max
A	4.25	4.85	B1	2.60	3.00
A1	2.30	3.00	e	2.40	2.70
A2	1.20	1.40	e1	4.95	5.25
b	0.60	0.90	L	12.60	14.40
b1	1.10	1.70	L1	2.40	4.00
c	0.40	0.70	⌀P	3.50	3.90
D	9.80	10.60			
B	15.20	16.20			



●Dimensions（TO-263)

Unit：mm

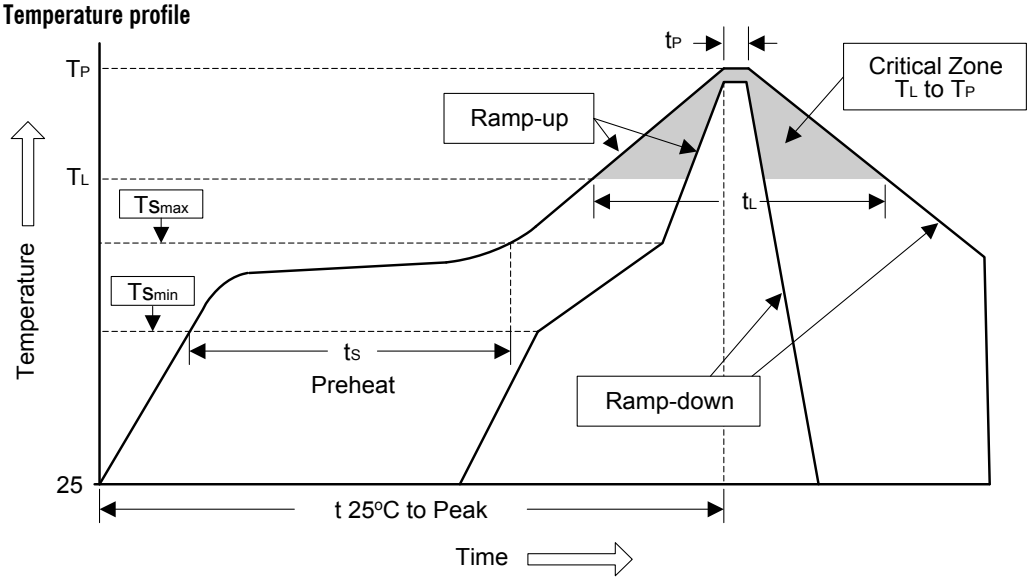
SYMBOL	min	max	SYMBOL	min	max
A	4.25	4.85	B1	1,20	1.80
A1	2.30	3.00	e	2.40	2.70
A2	1.20	1.40	L	4.80	5.60
b	0.60	0.90			
b1	1.10	1.70			
c	0.40	0.70			
D	9.80	10.60			
B	10.40	11.40			



• Soldering Methods for Lihomicro's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat - Temperature Min (Ts_{min}) - Temperature Max (Ts_{max}) - Time (min to max) (ts)	 100°C 150°C 60 to 120 sec	 150°C 200°C 60 to 180 sec
Tsmax to T_L - Ramp-up Rate	 <3°C/sec	 <3°C/sec
Time maintained above: - Temperature (T_L) - Time (t_L)	 183°C 60 to 150 sec	 217°C 60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec